

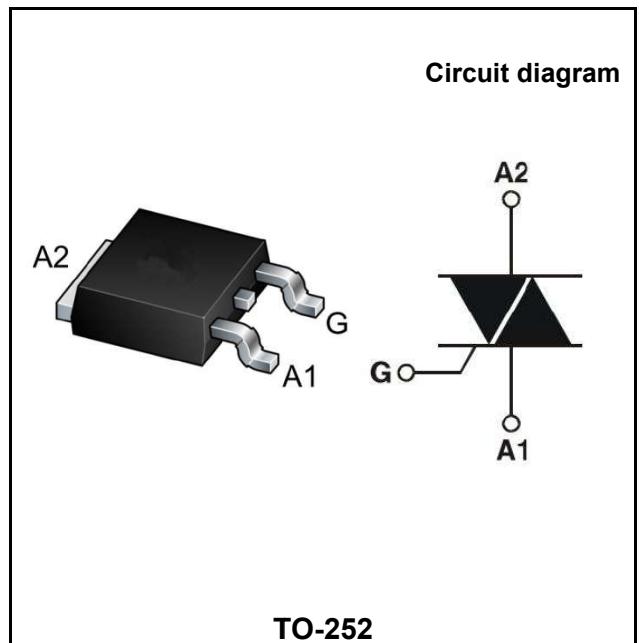
12A 4Quadrants TRIACs

Product Summary

Symbol	Value	Unit
$I_{T(RMS)}$	12	A
$V_{DRM} V_{RRM}$	600/800	V
V_{TM}	1.55	V

Features

With high ability to withstand the shock loading of large current, With high commutation performances, 4 quadrants products especially recommended for use on inductive load.



TO-252

Application

Washing machine, vacuums, massager, solid state relay, AC Motor speed regulation and so on.

Order Information

Part Number	Package	Marking	Delivery Form	Delivery Quantity
BT138D	TO-252	BT138 800E XXXX	12" T&R	2500PCS/Tape

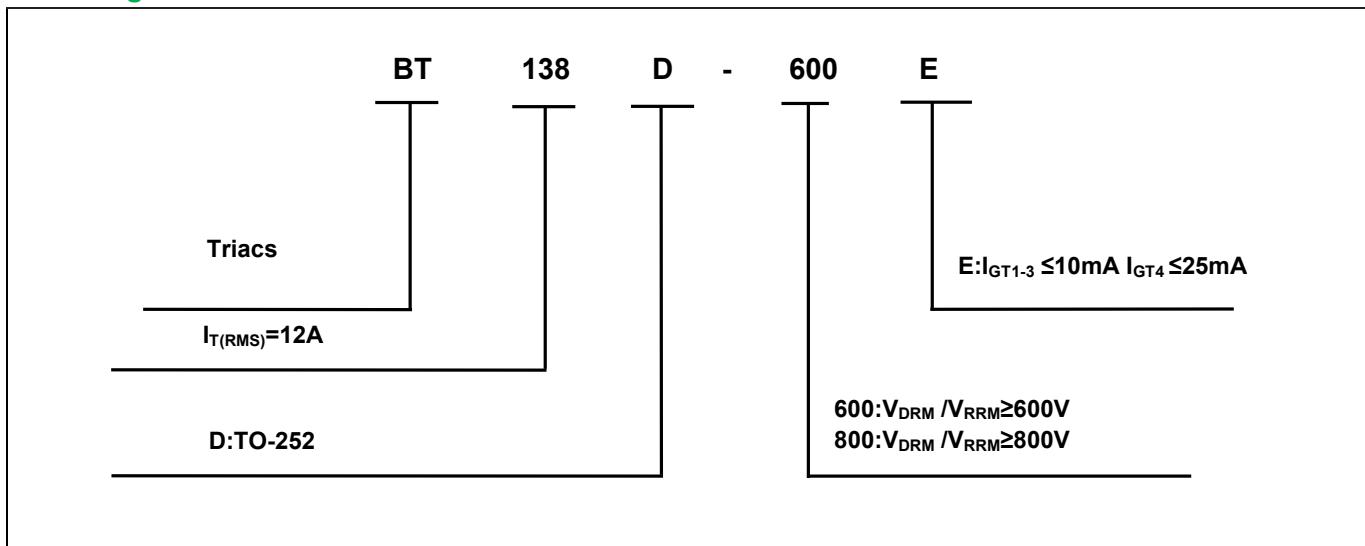
Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value		Unit
Repetitive peak off-state voltage	V_{DRM}	600/800		V
Repetitive peak reverse voltage	V_{RRM}	600/800		V
RMS on-state current	$I_{T(RMS)}$	12		A
Non repetitive surge peak on-state current (full cycle, F=50Hz)	I_{TSM}	95		A
I^2t value for fusing ($t_p=10ms$)	I^2t	45		A^2s
Critical rate of rise of on-state current ($ I_G = 2 \times I_{GT} $)	dI_T/dt	I - II - III IV	50 10	$A/\mu s$
Peak gate current	I_{GM}	2		A
Average gate power dissipation	$P_G (AV)$	0.5		W
Junction Temperature	T_J	-40~+125		°C
Storage Temperature	T_{STG}	-40 ~+150		°C

Electrical characteristics (TA=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Value		Unit
			Min	Max	
Gate trigger current	I _{GT}	V _D =12V I _T =0.1A T _j =25°C	I - II - III	-	10
			IV	-	25
Gate trigger voltage	V _{GT}		I - II - III - IV	-	1.3
Gate non-trigger voltage	V _{GD}	V _D =V _{DRM} T _j =125°C	0.2	-	V
latching current	I _L	V _D =12V I _{GT} =0.1A T _j =25°C	I - III - IV	-	30
			II	-	40
Holding current	I _H		I - II - III - IV	-	30
Critical-rate of rise of commutation voltage	dV _D /dt	V _D =2/3V _{DRM} Gate Open T _j =125°C	20	-	V/us
STATIC CHARACTERISTICS					
Forward "on" voltage	V _{TM}	I _{TM} =15A t _p =380μs	-	1.55	V
Repetitive Peak Off-State Current	I _{DRM}	V _D =V _{DRM} V _R =V _{RRM}	T _j =25°C	-	10
Repetitive Peak Reverse Current	I _{RRM}		T _j =125°C	-	1
THERMAL RESISTANCES					
Thermal resistance	R _{th(j-c)}	Junction to case(AC)	TYP.	1.4	°C/W
	R _{th(j-a)}	Junction to ambient	TYP.	70	°C/W

Ordering Information



Typical Characteristics

FIG.1: Maximum power dissipation versus RMS on-state current (full cycle)

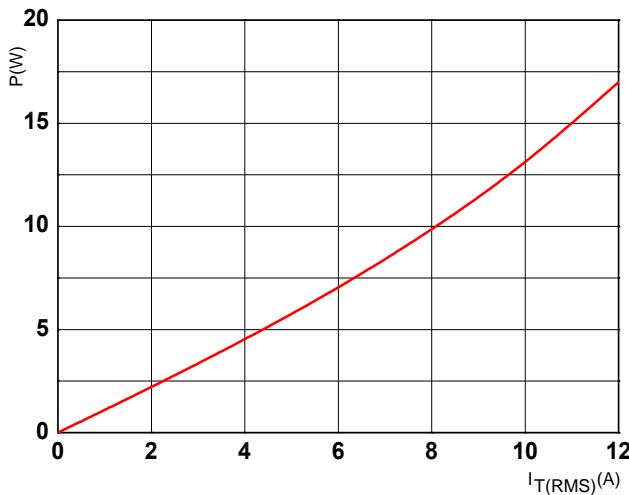


FIG.2: RMS on-state current versus case temperature (full cycle)

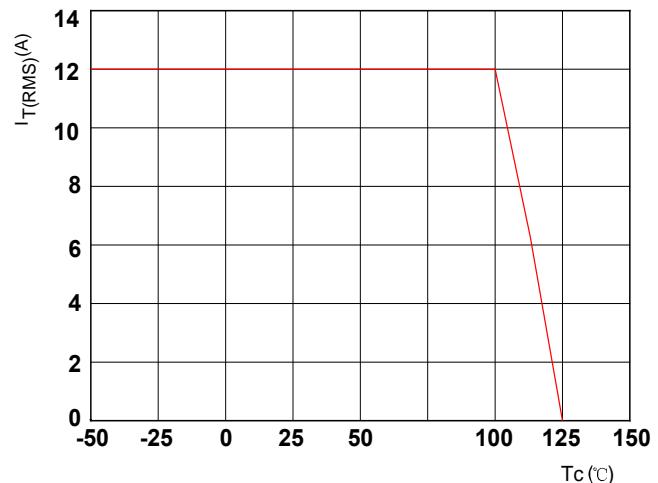


FIG.3: Surge peak on-state current versus number of cycles

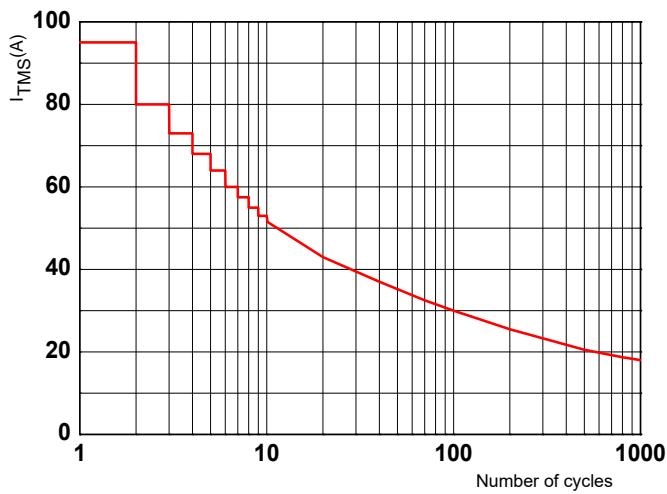


FIG.4: On-state characteristics (maximum values)

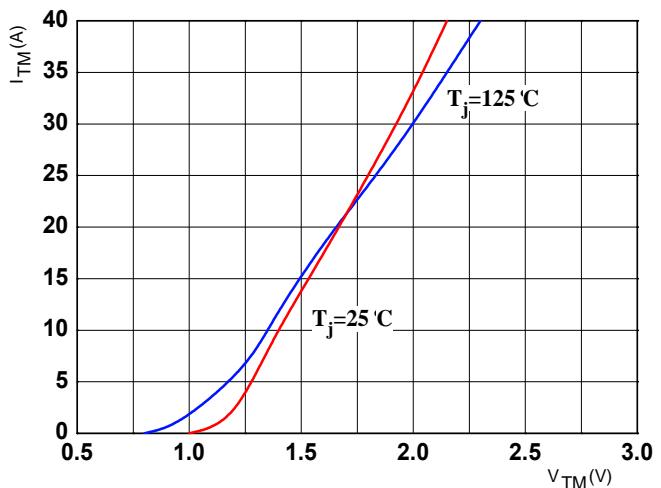


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10ms$

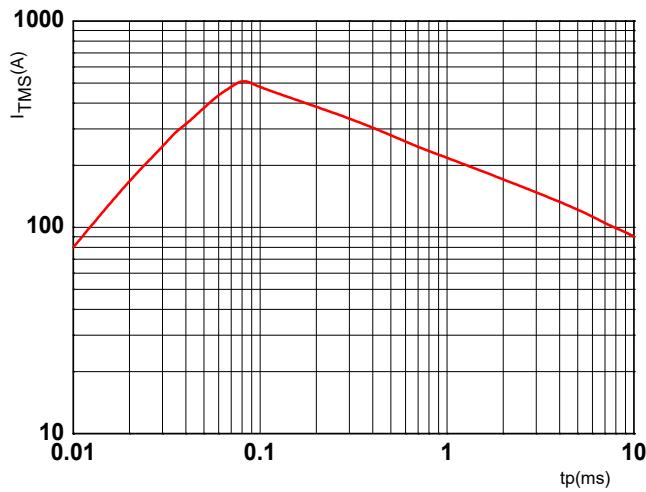
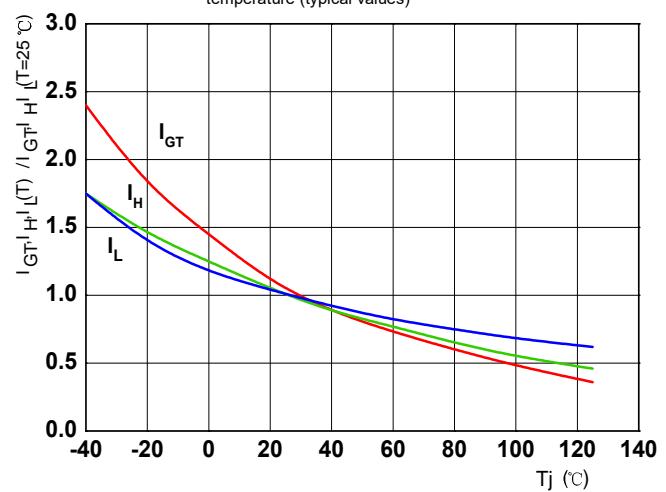
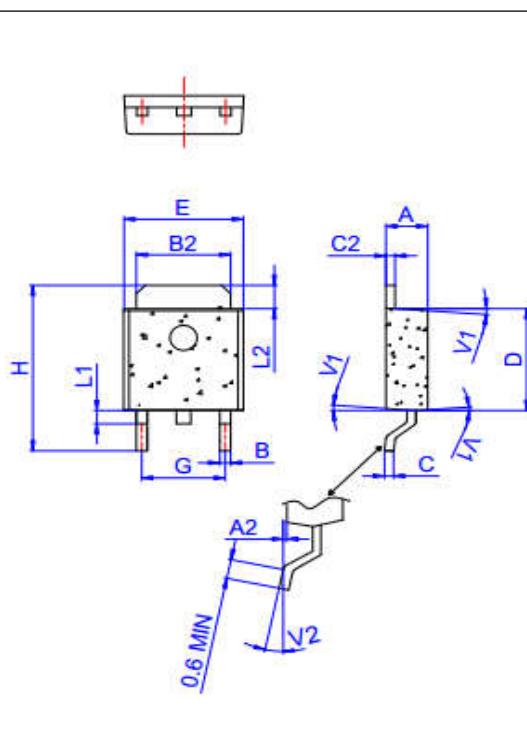


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature (typical values)



Package Information

TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.85	0.019		0.034
D	5.30		6.20	0.208		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°